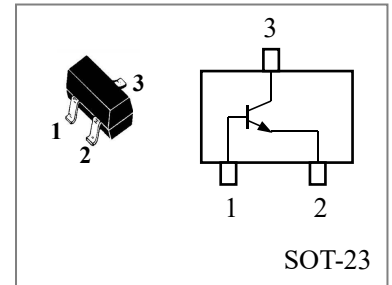


MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	20	V
Collector-Base Voltage	V_{CBO}	30	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	50	mA
Total Device Dissipation($T_A=25^\circ\text{C}$)	P_{tot}	225	mW
Thermal Resistance Junction to Ambient	$R_{(th)ja}$	556	$^\circ\text{C}/\text{W}$
Junction Temperature(Max)	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$

**GENERAL PURPOSE
TRANSISTOR NPN SILICON**
225mW、50mA、20V



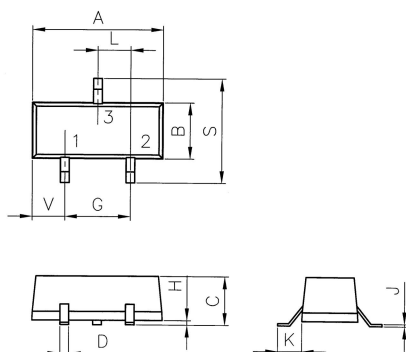
DEVICE MARKING

2SC2714Y=QY

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Test condition	Min	Typ	Max	Unit
Breakdown Voltage	$V_{(BR)CEO}$	$I_C=3\text{mA}, I_B=0$	20	—	—	V
	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	30	—	—	V
	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	3.0	—	—	V
Collector-Cutoff Current	I_{CBO}	$V_{CB}=15\text{V}, I_E=0$	—	—	0.05	μA
DC Current Gain	h_{FE}	$I_C=50\text{mA}, V_{CE}=1.0\text{V}$	20	—	—	—
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	—	—	0.40	V
Base – Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	—	—	1.0	V
Transition-Frequency	f_T	$V_{CE}=1.0\text{V}, I_C=3.0\text{mA}$	600	—	—	MHz

SOT-23



mm

	SOT-23	
	min	max
A	2.80	3.04
B	1.20	1.40
C	0.89	1.13
D	0.30	0.50
G	1.80	2.04
H	0.01	0.10
J	0.08	0.18
K	0.45	0.60
L	0.89	1.02
S	2.10	2.50
V	0.42	0.60